



DESCRIPTION:

The JST08K-600BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST08K-600BW snubberless triac is especially recommended for use on inductive loads. Package TO-252 is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	600	V
$I_{GT} / /$	60/50/50	

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600	V
RMS on-state current ($T_C 091^\circ\text{C}$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		88	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	A/s
Peak gate current ($t_p=20\text{ s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	2.5	kV
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ELECTRICAL CHARACTERISTICS (at $T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				90	
I_H	$I_T=100mA$		MAX.	50	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125$		MIN.	2000	V/s
$(dI/dt)_c$	$(dV/dt)_c=20V/s$, $T_j=125$		MIN.	12	A/ms
t_{on}	$I_G=80mA$ $I_A=400mA$ $I_R=40mA$ $T_j=25$		TYP.	5	s
t_{off}				50	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=11A$ $t_p=380$ s	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.8	V
R_D	Dynamic resistance	$T_j=125$	44	m
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	A
I_{RRM}		$T_j=125$	0.25	mA

THERMAL RESISTANCES

JST08K-600BW

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

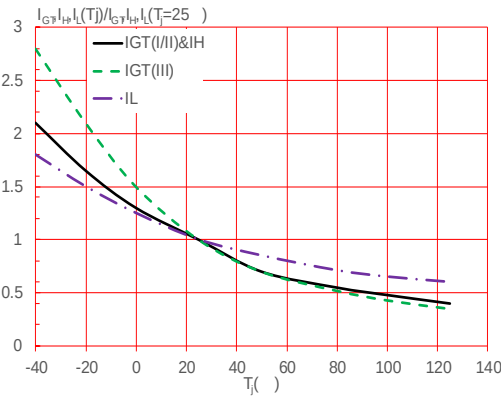
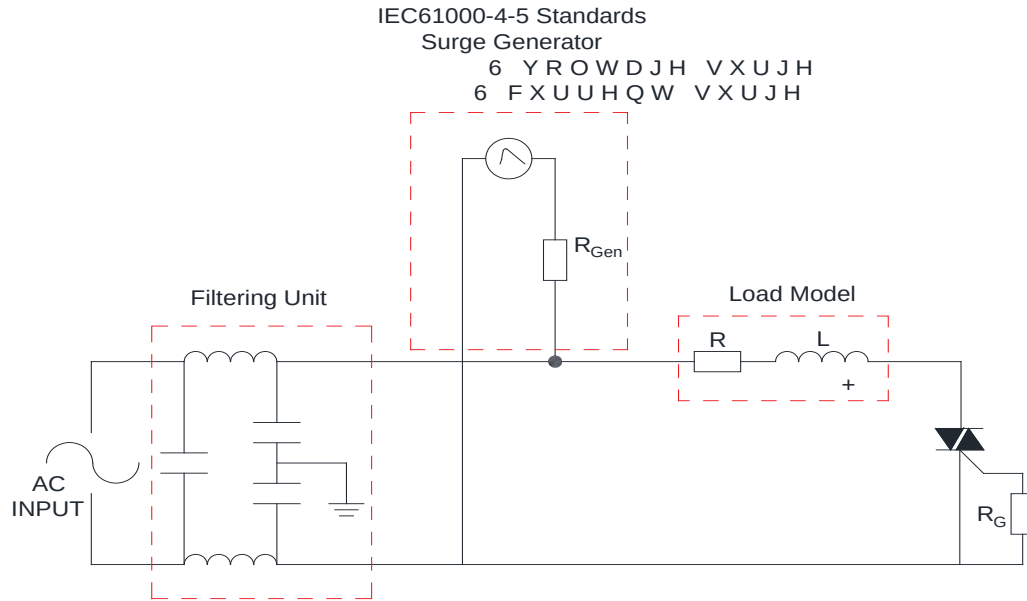


FIG.8 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST08K-600BW	600	50	TO-252	80	Tube
JST08K-600BW-TR				2,500	Tape & Reel

Document Revision History

Date	Revision	Changes
Apr.12, 2023	A.1	

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